

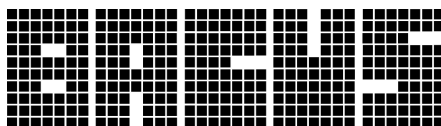
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Peter D. Buck
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Contents

vii	<i>Authors</i>
xi	<i>Conference Committee</i>

ADVANCED WRITERS

9985 05	MBMW-101: World's 1st high-throughput multi-beam mask writer (Invited Paper) [9985-4]
9985 06	The technical consideration of multi-beam mask writer for production [9985-5]
9985 07	Improvement of Electron Beam Lithography modeling for overdose exposures by using Dill transformation [9985-6]
9985 08	Electron beam mask writer EBM-9500 for logic 7nm node generation [9985-7]

ADVANCED MATERIALS

9985 0A	NXE pellicle: development update [9985-9]
9985 0B	Development of a novel closed EUV pellicle for EUVL manufacturing [9985-10]
9985 0C	Introducing the EUV CNT pellicle [9985-11]
9985 0D	Development of advanced multi-tone mask by using two different transmittance modulation materials [9985-12]

STUDENT SESSION

9985 0G	Influence of non-uniform intensity distribution of deformed pellicle for N7 patterning [9985-14]
9985 0I	Impact of noise sources and optical design on defect sensitivity for EUV actinic pattern inspection [9985-16]
9985 0K	Observation results of actual phase defects using micro coherent EUV scatterometry microscope [9985-18]

INSPECTION AND METROLOGY

9985 0L	Reticle inspection equipment productivity increase using SEMI specification for reticle and pod management [9985-57]
9985 0M	YieldStar based reticle 3D measurements and its application [9985-20]

9985 0N **Evaluation of photomask flatness compensation for extreme ultraviolet lithography** [9985-21]

9985 0O **Take a byte out of MEEF: VAMPIRE: Vehicle for Advanced Mask Pattern Inspection Readiness Evaluations** [9985-22]

MASK MANUFACTURABILITY

9985 0R **Mask manufacturing of advanced technology designs using multi-beam lithography (part 2)** [9985-25]

9985 0T **Analyzing EUV mask costs** [9985-27]

END USER ANALYSIS

9985 0V **Comparing curvilinear vs Manhattan ILT shape efficacy on EPE and process window** [9985-71]

9985 0W **Experimental verification of AI decomposition-based source optimization for M1 two-bar building blocks in 0.33NA EUVL** [9985-30]

9985 0X **Quantifying imaging performance bounds of extreme dipole illumination in high NA optical lithography** [9985-31]

9985 0Y **UDOF direct improvement by modulating mask absorber thickness** [9985-32]

PROCESS

9985 12 **Comparative study on PS material of EAPSM for flat panel display** [9985-54]

9985 13 **Correction of placement error in EBL using model based method** [9985-112]

CLEANING AND REPAIR

9985 15 **Megasonic cleaning strategy for sub-10nm photomasks** [9985-38]

9985 16 **Identification of a new source of reticle contamination** [9985-39]

9985 17 **Phase-independent multilayer defect repair for EUV photomasks** [9985-40]

ADVANCED EDA

9985 19 **Software-based data path for raster-scanned multi-beam mask lithography** [9985-42]

9985 1A **OPC care-area feedforwarding to MPC** [9985-43]

9985 1C **The performance improvement of SRAF placement rules using GA optimization** [9985-45]

ALTERNATIVE LITHOGRAPHY

9985 1D **Writing next-generation display photomasks (Invited Paper)** [9985-46]

9985 1G **Nanoimprint wafer and mask tool progress and status for high volume semiconductor manufacturing** [9985-49]

POSTER SESSION: ADVANCED MATERIALS AND ADVANCED WRITERS

9985 1H **Prototyping 9-inch size PSM mask blanks for 450mm wafer process (2016)** [9985-51]

9985 1I **Evaluation of the properties of the permeability film material using cellulose nanofibers** [9985-52]

9985 1J **7-nm e-beam resist sensitivity characterization** [9985-86]

POSTER SESSION: STUDENTS

9985 1K **Mechanical stress induced by external forces in the extreme ultraviolet pellicle** [9985-55]

9985 1L **Investigation of fabrication process for sub 20-nm dense pattern of non-chemically amplified electron beam resist based on acrylic polymers** [9985-56]

POSTER SESSION: INSPECTION AND METROLOGY

9985 1M **The CD control improvement by using CDSEM 2D measurement of complex OPC patterns** [9985-19]

9985 1N **The study of CD side to side error in line/space pattern caused by post-exposure bake effect** [9985-36]

9985 1P **Scanning coherent scattering methods for actinic EUV mask inspection** [9985-60]

9985 1Q **To repair or not to repair: with FAVOR there is no question** [9985-61]

9985 1S **Improvement of photomask CD uniformity using spatially resolved optical emission spectroscopy** [9985-64]

9985 1T **Development of actual EUV mask observation method for micro coherent EUV scatterometry microscope** [9985-66]

9985 1W **Registration performance on EUV masks using high-resolution registration metrology** [9985-67]

POSTER SESSION: MASK MANUFACTURABILITY AND END USER

- 9985 1X **Correction of deflection under mask's own weight by bending mask technology** [9985-29]
- 9985 1Y **Defect inspection and printability study for 14 nm node and beyond photomask** [9985-68]
- 9985 1Z **Reticle decision center: a novel applications platform for enhancing reticle yield and productivity at 10nm technology and beyond** [9985-69]
- 9985 20 **EBL2: high power EUV exposure facility** [9985-70]
- 9985 21 **Wafer hot spot identification through advanced photomask characterization techniques** [9985-89]

POSTER SESSION: CLEANING AND REPAIR

- 9985 22 **Defect management on photomasks with dry treatment assistance** [9985-72]
- 9985 23 **Carbon dioxide gas purification and analytical measurement for leading edge mask and wafer cleaning** [9985-73]
- 9985 24 **Acoustic characterization of two megasonic devices for photomask cleaning** [9985-74]

POSTER SESSION: ADVANCED EDA

- 9985 25 **Auto-score system to optimize OPC recipe parameters using genetic algorithm** [9985-76]
- 9985 27 **OPC model sampling evaluation and weakpoint "in-situ" improvement** [9985-78]
- 9985 28 **Suppressing rippling with minimized corner rounding through OPC fragmentation optimization** [9985-79]
- 9985 2A **Combining mask and OPC process verification for improved wafer patterning and yield** [9985-81]

POSTER SESSION: ALTERNATIVE LITHOGRAPHY

- 9985 2B **Fundamental study of green EUV lithography using natural polysaccharide for the use of pure water in developable process** [9985-82]
- 9985 2C **Approach of UV nanoimprint lithography using template with gas-permeable and gaseous adsorption for reduction of air-trapping issue** [9985-83]
- 9985 2D **Production and evaluation of measuring equipment for share viscosity of polymer melts included nanofiller with injection molding machine** [9985-84]
- 9985 2E **High-performance fabrication process for 2xnm hole-NIL template production** [9985-85]